


AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph [0003] with the following amended paragraph:

 [0003] In the field of semiconductor devices, there is increasing integration and miniaturization of the elements. In order to respond to this, semiconductor manufacturing processes are carried out using high frequency sputtering devices for such operations as filling film inside minute holes. Figure 10 is a sectional front view of a ~~conventional~~ high frequency sputtering device. A circular cathode 14 is mounted at the mouth of the upper part of a processing chamber 10 by means of an insulator 12. An interface device 16, filter 18 and high frequency power supply 20 are connected in series with this cathode 14. A target 22 is mounted on the lower face of the cathode 14. A cylindrical grounding shield 24 is mounted on the processing chamber 10 in such a way that it surrounds the cathode 14 and the target 22. As shown in a magnified view in Figure 11, the gap between the grounding shield 24 and the cathode 14 is narrow, being approximately 2 mm. The size of this gap is sufficiently smaller than the sheath thickness necessary to support plasma, in order to prevent plasma from entering the gap. The substrate holder 26 is arranged inside the processing chamber 10 so as to be opposite the target 22. A substrate 28 is mounted on this substrate holder 26.